



# Quantum Dot Modeling using NEMO 3-D

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**Work performed in collaboration with**  
**R. Chris Bowen (TI), Fabiano Oyafuso, Tom Cwik (JPL),**  
**Tim Boykin (U Alabama--Huntsville)**

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# Presentation Outline



- **Motivation**
- **What is a Quantum Dot ?**
- **Quantum Dot Modeling (NEMO 3-D):**
  - **Tight Binding Parameterization**
  - **Strain**
  - **Alloy Disorder**
  - **Interface Interdiffusion**
  - **Parallelization**
  - **Nanotubes**
- **Conclusion / Future Vision**





# Technology Push



## Toward Fundamental Limitations

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### Commercial market pushes computing performance (FLOPS/weight/power):

- Enabled by device miniaturization
- Enabled by chip size increase
- Limited by: Costs of fabrication
- Limited by: Discrete atoms/electrons





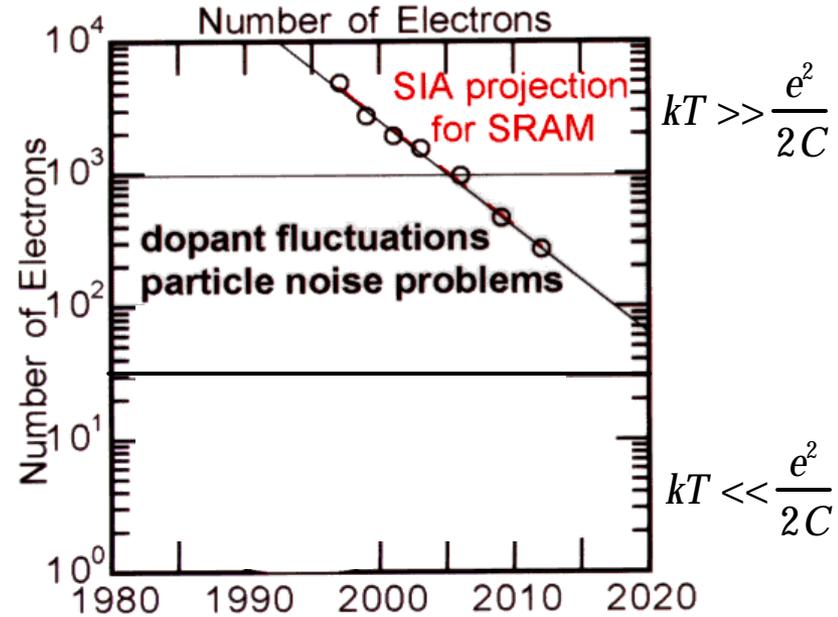
# Technology Push



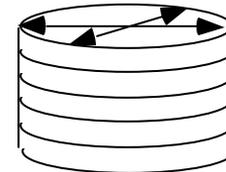
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2-D Lithography feature





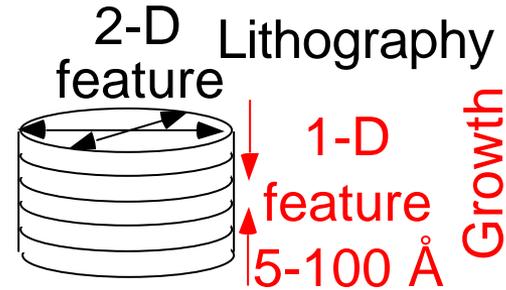
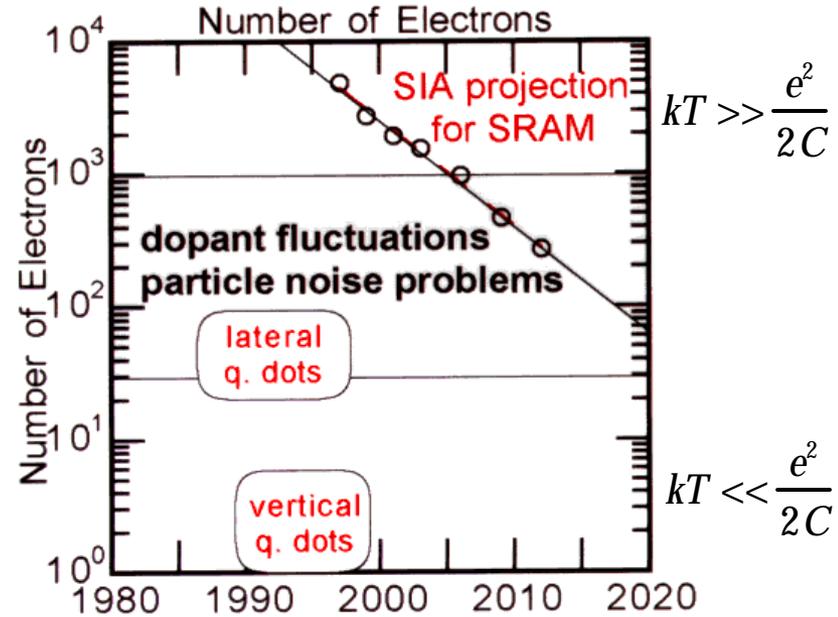
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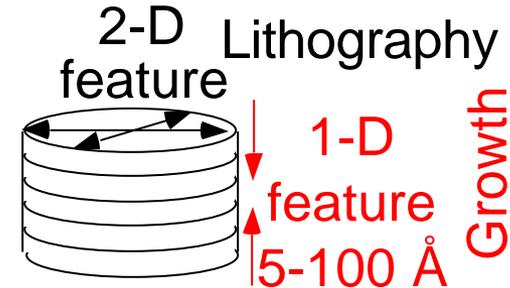
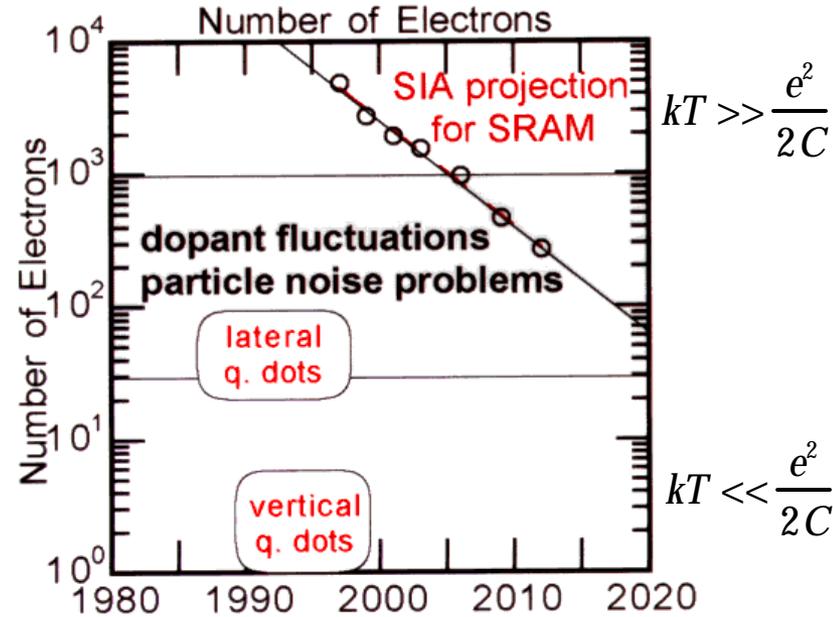
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### Quantum Dots Push beyond SIA with near and long term applications

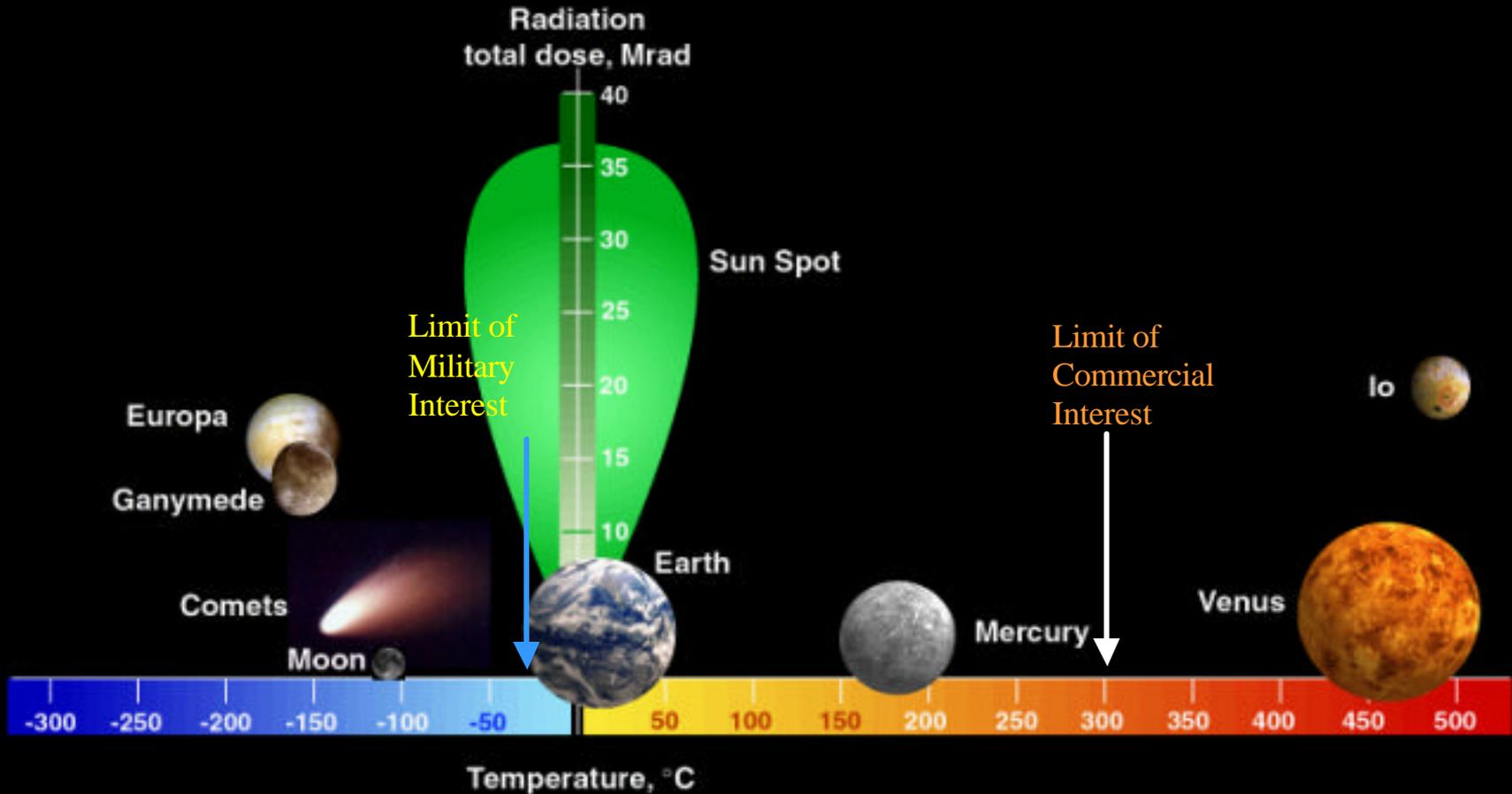
- Detectors / lasers
- Memory and logic



*Quantum dots go beyond the SIA roadmap and enable near and long term NASA applications*



# Planetary Extreme Environments



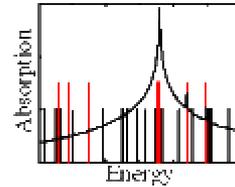
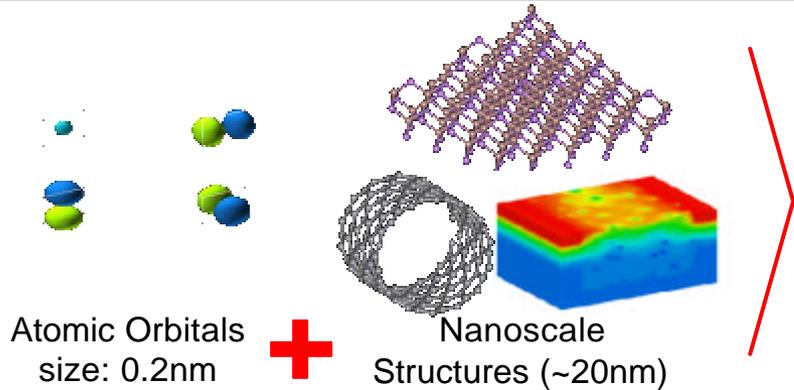
*NASA radiation and temperature requirements extend beyond commercial and military interest*



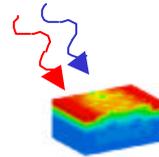
Quantum Dot Modeling - Development of Bottom-Up Nanoelectronic Modeling Tool

# Nano-scale Device Analysis / Synthesis

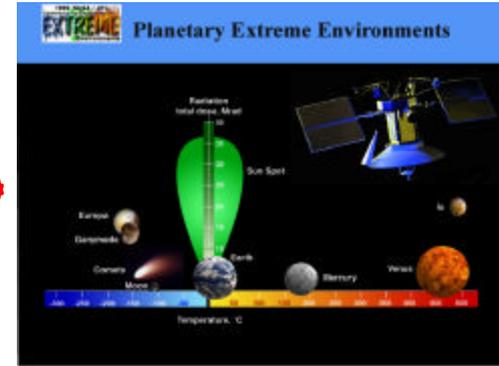
## Development of a Bottom-Up Nanoelectronic Modeling Tool



New Devices for  
**Sensing** and  
**Computing**



Analyze Devices:  
**Environment**  
and **Failures**



### Assertions / Problems:

- Nanoscale electronic structures are built today! The design space is huge: choice of materials, compositions, doping, size, shape
- Radiation on today's sub-micron devices modifies the electronics on a nanoscale.

### Approach:

- Deliver a 3-D atomistic simulation tool
- Enable analysis of arbitrary crystal structures, particles, atom compositions and bond/structure at arbitrary temperatures and ambient electric and magnetic fields.

### Collaborators:

- U. of Alabama, Ames, Purdue

### NASA Relevance:

- Enable new devices needed for NASA missions beyond existing industry roadmap:
  - Water detection -> 2-5µm Lasers and detectors.
  - Avionics -> High density, low power computing.
- Analyze state-of-the-art devices for non-commercial environments:
  - Europa -> Radiation and low temperature effects. Aging and failure modes.
  - Jovian system -> Magnetic field effects
  - Venus -> high temperature materials: SiGe

### Impact:

- Low cost development of revolutionary technology
- Narrow empirical/experimental search space



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*Modeling will narrow the empirical search space!*





# What is a Quantum Dot ?



## Basic Application Mechanisms

---

### Physical Structure:

- Well conducting domain surrounded in all 3 dim. by low conducting region(s)
- Domain size on the nanometer scale

### Electronic structure:

- Contains a countable number of electrons
- Electron energy may be quantized -> artificial atoms (coupled QD->molecule)





# What is a Quantum Dot ?



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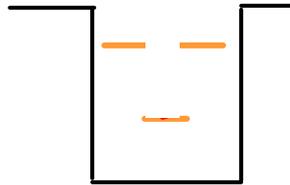
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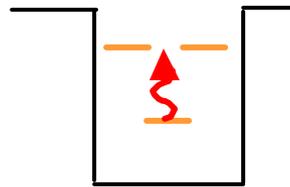


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Photon  
Absorption



**Detectors/  
Input**





# What is a Quantum Dot ?

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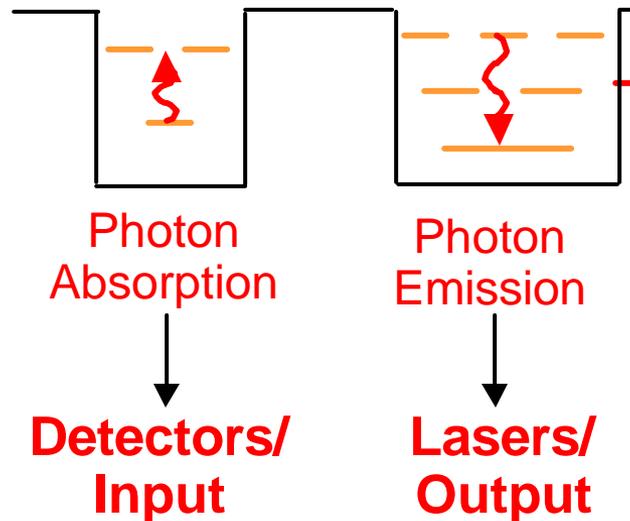


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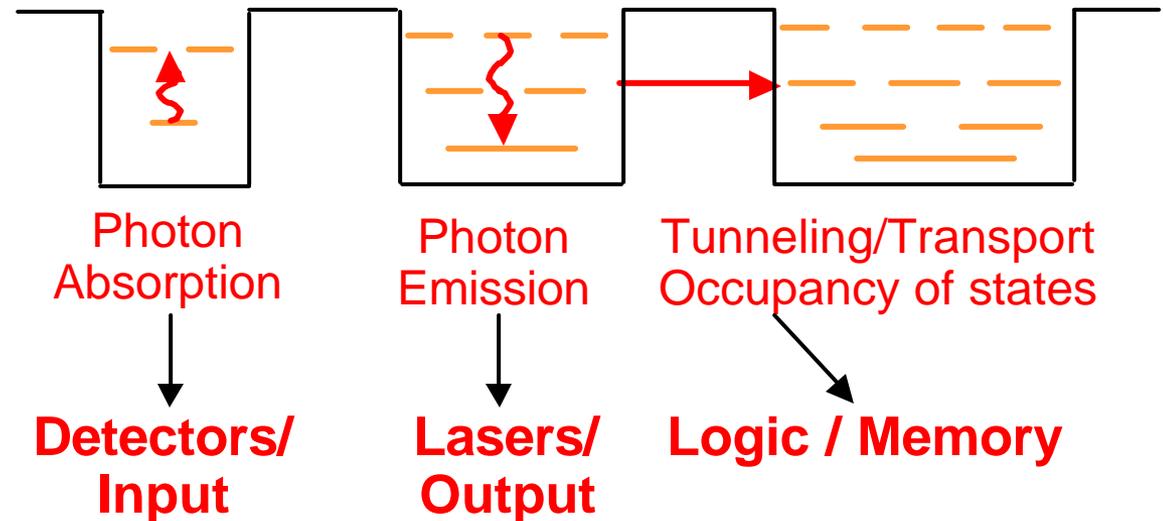
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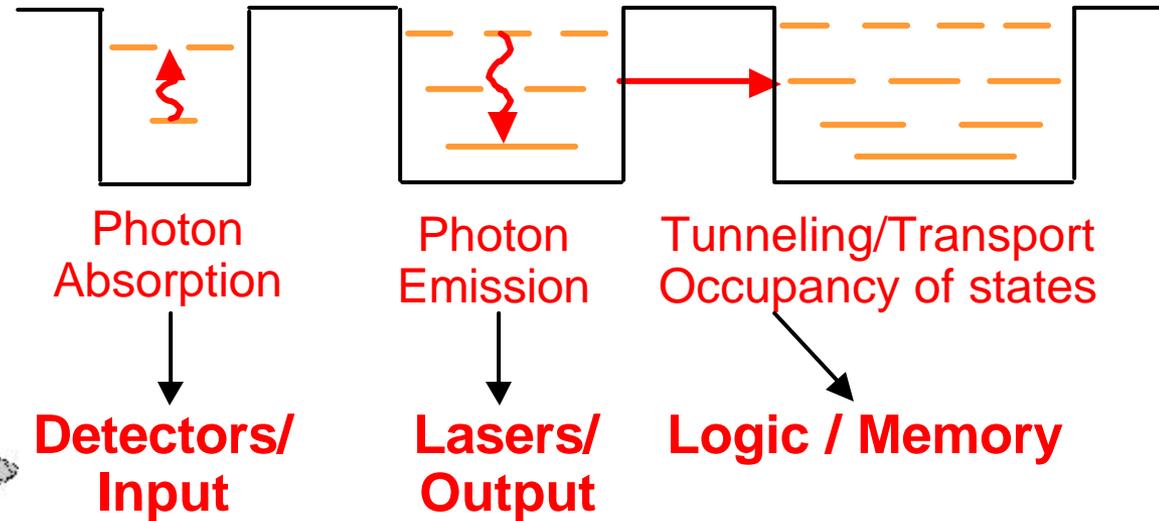
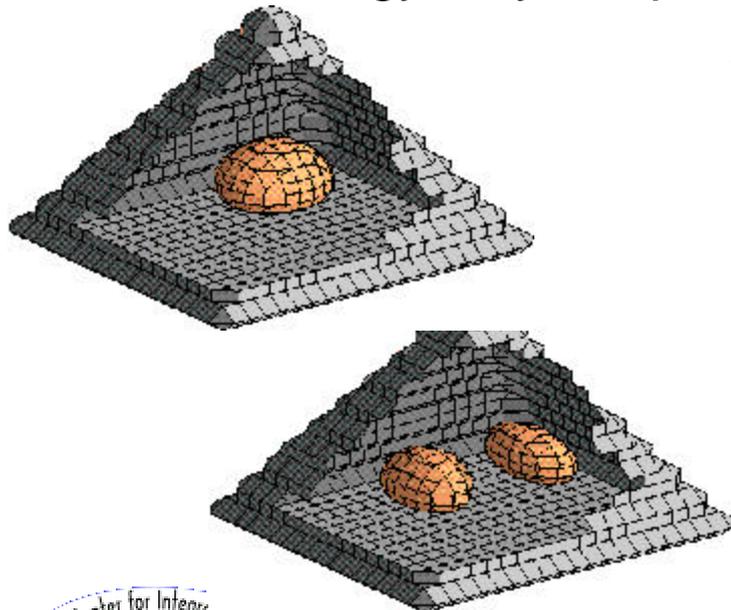
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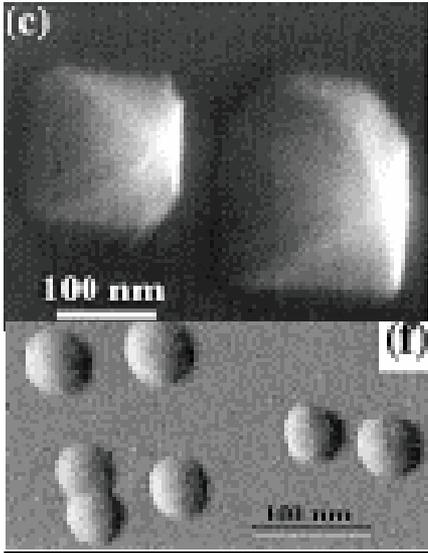


*Quantum dots are artificial atoms that can be custom designed for a variety of applications*





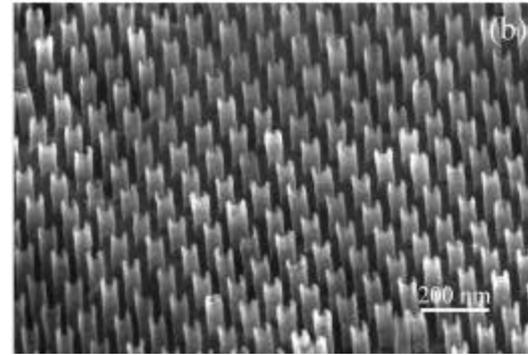
# Nanotechnology / Nanoelectronic Example Implementations



**Self-assembled** ,  
InGaAs on GaAs.

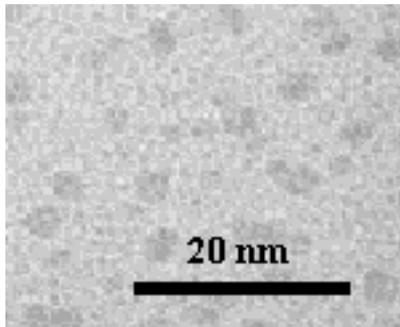
Pyramidal or  
dome  
shaped

R.Leon,JPL(1998)



**Nanotube  
Arrays,**

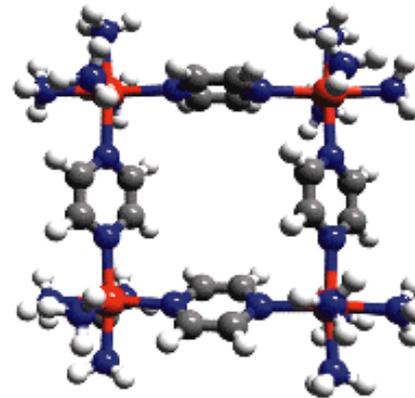
Jimmy Xu,  
Brown Univ.  
(1999)



**Nanocrystals:**

Si implanted in SiO<sub>2</sub>

Atwater, Caltech  
(1996)



**Molecular Dots**

Ruthenium-based  
molecule

Ru<sub>4</sub>(NH<sub>3</sub>)<sub>16</sub>(C<sub>4</sub>H<sub>4</sub>  
N<sub>2</sub>)<sub>410+</sub>

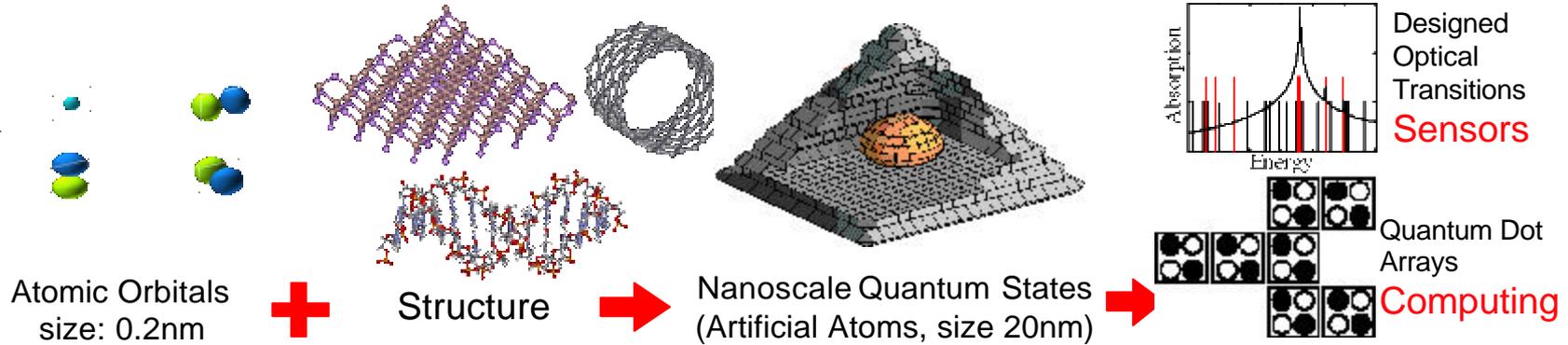
proposed by Marya  
Lieberman, Notre  
Dame (1999)

*Low Dimensional quantum confinement  
can be achieved in a variety of material systems*





# Technical Approach



## Problem:

Nanoscale device simulation requirements:

- Cannot use bulk / jellium descriptions, need description of the material atom by atom  
=> use pseudo-potential or local orbitals
- Consider finite extension, not infinitely periodic  
=> local orbital approach
- Need to include about one million atoms.  
=> need massively parallel computers
- The design space is huge: choice of materials, compositions, doping, size, shape.  
=> need a design tool

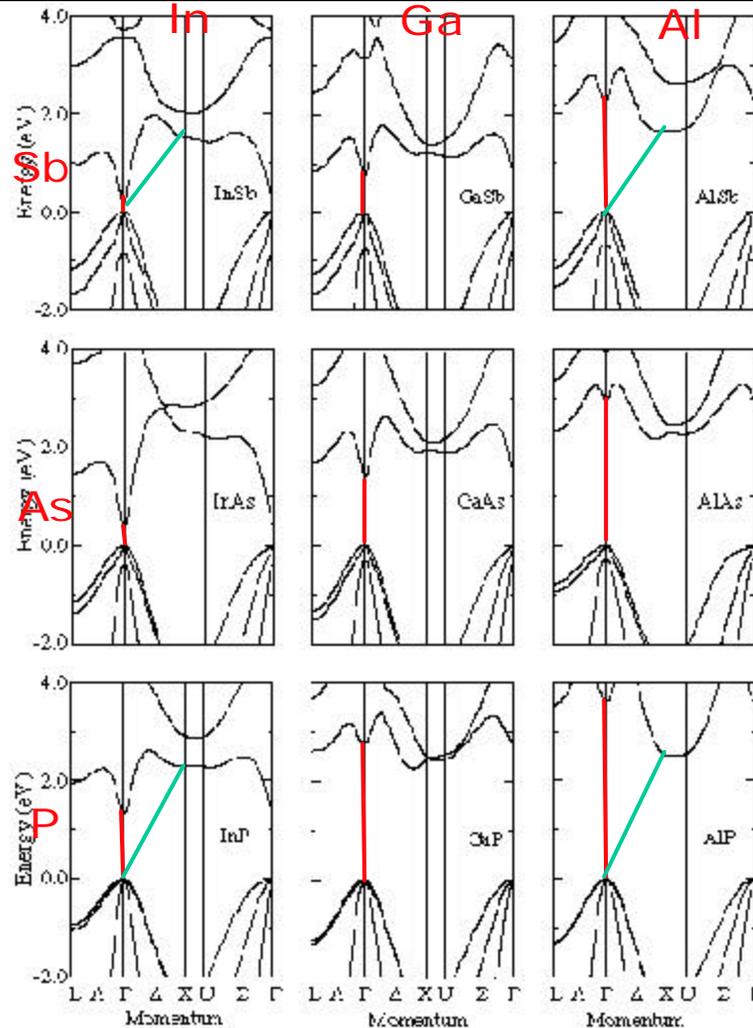
## Approach:

- Use local orbital description for individual atoms in arbitrary crystal / bonding configuration
  - Use s, p, and d orbitals.
  - Use genetic algorithm to determine material parameter fitting
- General structure input → nanotube
- Develop efficient parallel algorithms to generate eigenvalues/vectors of very large matrices (N=40million for a 2 million atom system).
- Compute mechanical strain in the system.
- Alloy disorder → linewidth broadening
- Interface interdiffusion

*Realistic material description at the atomic level enables simulation of realistic nanoelectronic devices.*



# Genetic algorithm based material parameter analysis



Problem:

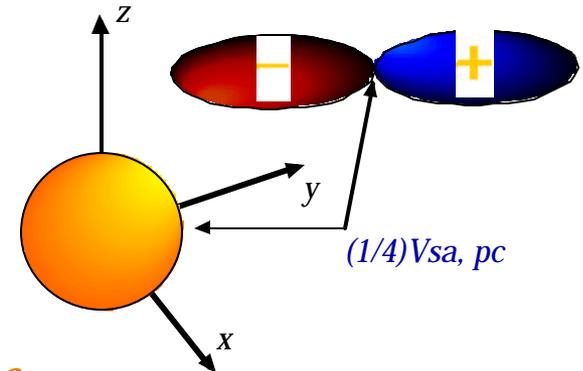
- Want atomistic / orbital based material description.
- Need to fit 15-30 orbital interaction energies to 20-30 material properties (bandgaps and masses)

Approach:

- Use massively parallel genetic algorithm to perform multidimensional optimization

Results/Impact:

- Established a 3x3 array of materials and their parameters that are the building blocks of quantum dots.
- Enable the atomistic simulation of quantum dots.



*Genetic algorithm enabled the establishment of a material basis set.*





# Mechanical Strain Calculations

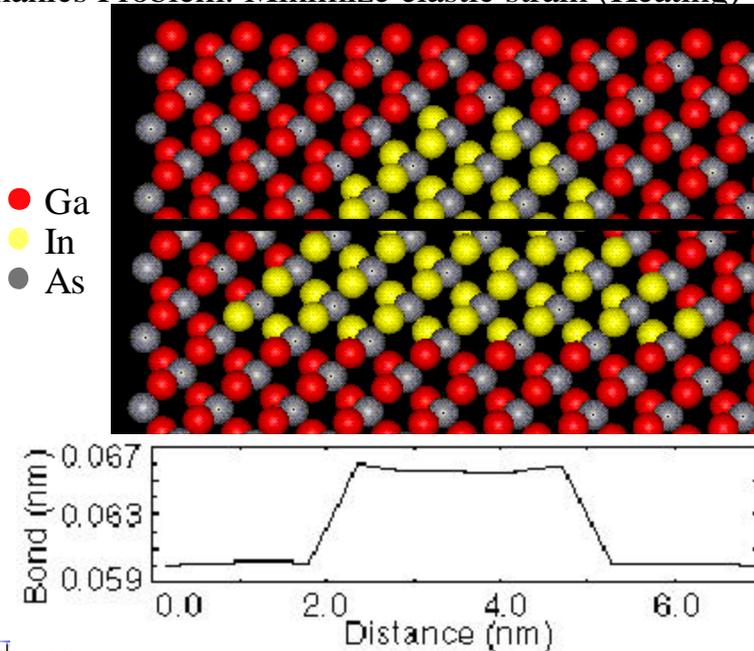
## Problem:

- Self-assembly dot formation due to strain
- Small mechanical strain (5% bond length)  
→ dramatic effects on electronic structures

## Approach:

- Nanomechanical strain calculation
- Nanoelectronic strain calculation.

Mechanics Problem: Minimize elastic strain (Keating)



## Results:

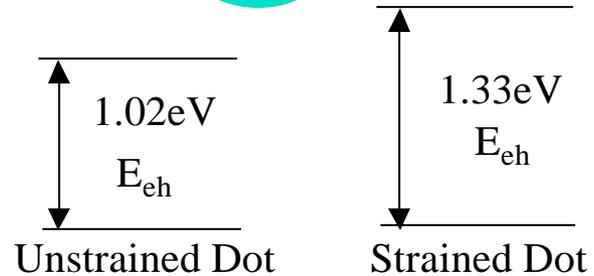
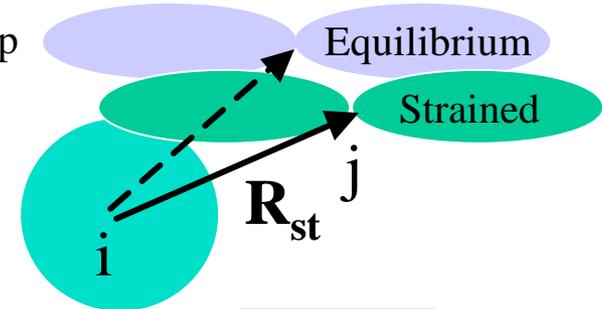
- Implemented a mechanical strain model.
- Implemented atomistic bandstructure model that comprehends strain.

## Impact:

- Can simulate realistic quantum dots.
- Can estimate optical transition energies properly.

Electronics Problem: Effect of overlap changes

Orbital overlap changes  
→ bandgaps and masses



Pyramidal InAs Dot Simulation

Base: 7nm x 7nm Height: 3nm Embedded in GaAs

*Small strain has dramatic effects on the electronic structure.*



# Alloy Disorder in Quantum Dots

## Problem:

- Cations are randomly distributed in alloy dots.
- Does alloy disorder limit electronic structure uniformity for dot ensembles?

## Approach:

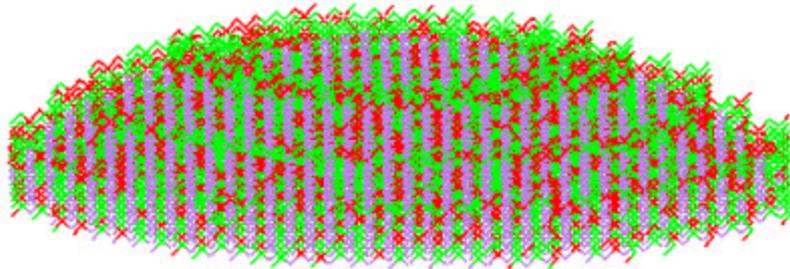
- Simulate a statistical ensemble of alloyed dots.
- Requires atomistic simulation tool.

## Results:

- Simulated 50 dots with random cation distributions.
- Inhomogeneous broadening factor of 9.4 meV due to alloy disorder.

## Impact:

- Fundamental uniformity limit for ensemble of alloy-based quantum dots.

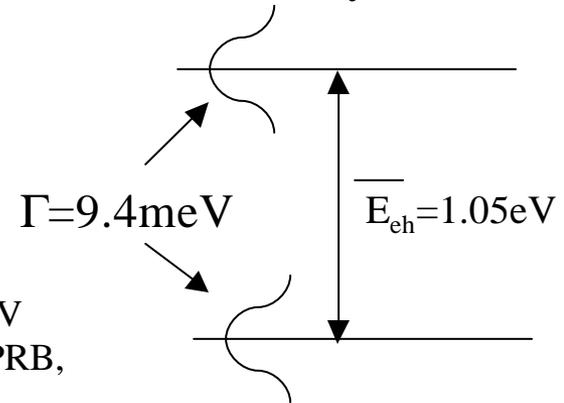


**In<sub>0.6</sub>Ga<sub>0.4</sub>As** Lens Shaped Dot

(Diameter=30nm, Height=5nm, GaAs embedded)

In and Ga atoms are randomly distributed  
Inhomogeneous Broadening?

## Simulation of Alloy Dot Ensemble



Measured  
 $\Gamma = 34.6 \text{ meV}$   
(R. Leon, PRB,  
58, R4262)

9.4meV Theoretical Lower Limit

*Alloy disorder presents a theoretical lower limit on optical linewidths*



# Atomistic Grading Simulation

## Problem:

- Quantum dot interfaces may not be sharp.
- There may be cation redistribution around the interface => grading of the concentration.
- How does the interfacial grading affect the electronic structure?

## Approach:

- Simulate quantum dot atomistically with graded interfaces as a function of interdiffusion length.

## Results:

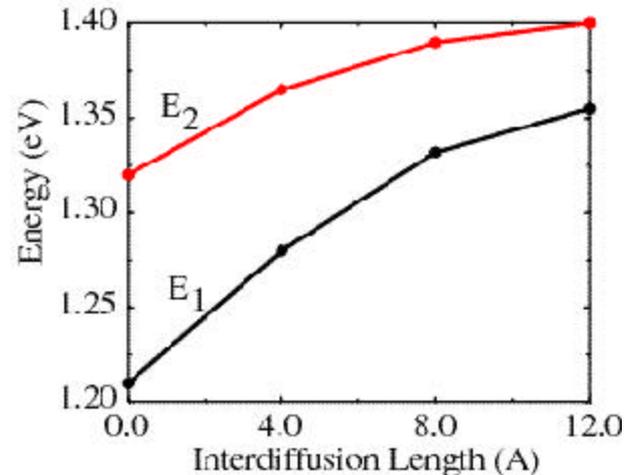
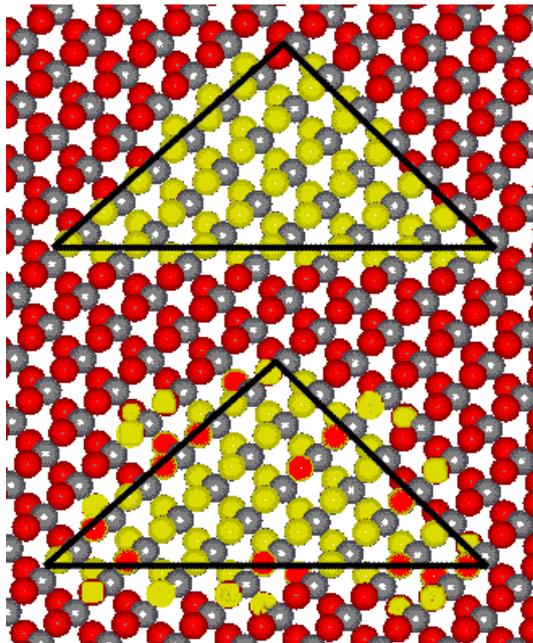
- More Ga in the quantum dot raises the energy of the transition energies.
- Less Ga in the barriers softens the barriers, reduces the binding of the excited states to the quantum dot and reduces  $\Delta E = E_2 - E_1$ .

## Impact:

- Verify experimentally suggested interdiffusion process may be responsible for blue shift and reduction in  $\Delta E$ .

## Cartoon Visualization of Interdiffusion

Slice through 2 Qdots with thickness of 3 atoms - with and without interdiffusion



Pyramidal InAs in GaAs, Diameter=10nm, Height=4.2nm  
5 samples per data point

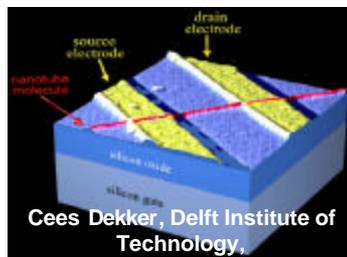
*Interdiffusion widens the bandgap  
=> blueshift*



# Incorporate Arbitrary Molecular Files → Nanotubes

## Background:

- Carbon nanotubes are currently explored for electronic and structural applications.



## Objective/Motivation:

- Simulate optical interactions and electron transport in nanotubes

## Problem:

- Need nanotube structural information.
- We do not have that expertise.

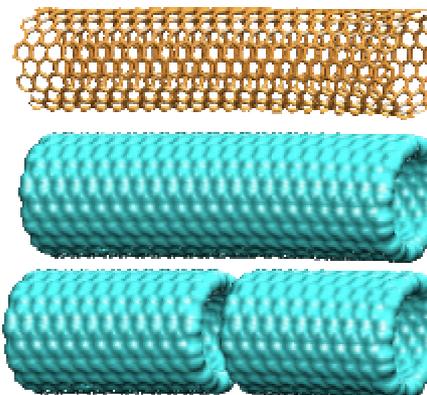
## Approach:

- Expanded code to read standard chemical structure file format.
- Get structural information from other researchers.

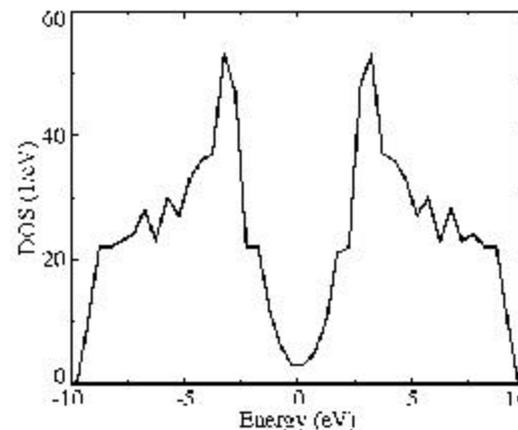
## Result:

- Simulated nanotube ground states and density of states.

## Preliminary Data



Finite size nanotube ground and excited state



Density of States

*We can input molecular dynamics based files and perform electronic structure calculations*





# Code Parallelization

## Problem:

- Need to calculate eigenvalues of a complex matrix of the order of 40 million.  
=> must parallelize code

## Approach:

- Compare Origin 2000 with distributed memory beowulf.
  - beowulf: 450 MHz, 32 nodes, 500 MB/node
  - Origin 2000: 300 MHz, 128 cpu, 64 GB

## Vision:

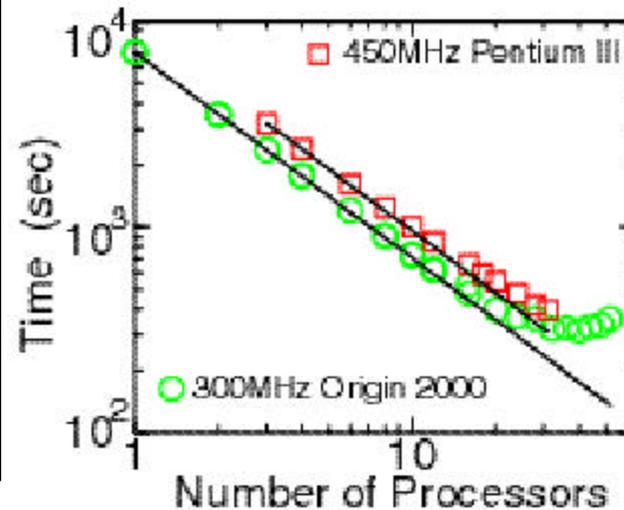
- Utilize a designated beowulf cluster of PC's as a workhorse for these simulations. Each node might have 1-4 shared memory CPUs on one motherboard.

## Results:

- Inexpensive commodity cluster scales competitively with shared memory Origin 2000.

## Impact:

- Enabled simulation of 2 million atom systems with 20 orbitals on each atom  
=> matrix of order 40million



Compare Origin 2000 vs. Beowulf: 10 Lanczos Iterations for a 1million atom system.

*Cluster of commodity PC's can beat a supercomputer for our problem*





## Future Plans

---

- Simulation of ensembles of alloyed quantum dots
  - Study fundamental limit of spectral lines due to alloy disorder
- Simulation of many-body effects via configuration interaction
  - Simulate optical transitions including effects of excitons
- Electron transport through quantum dot
  - Explore design possibilities for electronic transport devices
- “Super-scaled” tight-binding model to treat large arrays of quantum dots
- Transport through Nanotubes
- Develop a world-class 3-d nanoelectronic modeling tool

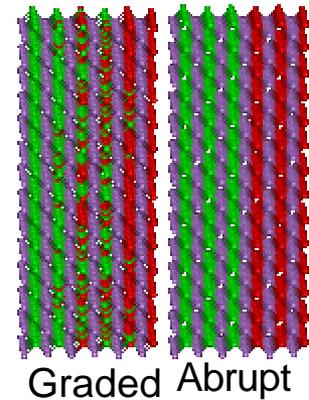
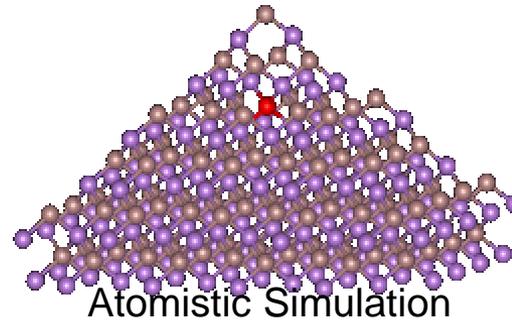




# Conclusions / Future Vision

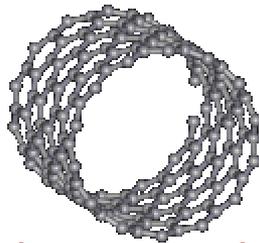
- Parallelization ( $2 \times 10^6$  atoms)
- Graded junctions, alloy disorder, strain
- Made significant progress towards a general atomistic simulation tool
- Envision this tool to have impact on quantum dots, end of SIA roadmap issues, and molectronics.

## Quantum Dots Grading

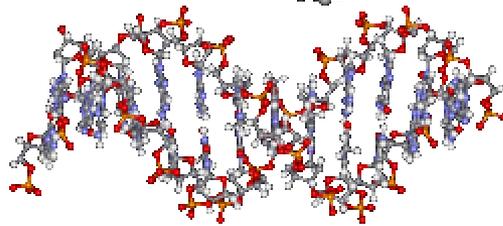


## Transport in Molecules

Carbon Nanotubes

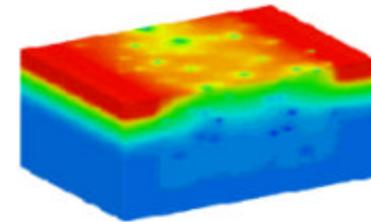


DNA

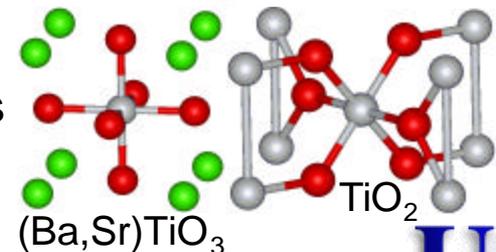


## End of SIA Roadmap

Dopant Fluctuations in Ultra-scaled CMOS



Electron Transport in Exotic Dielectrics



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*The best is still to come!*





# Backup Foils





## Technical Accomplishments (Physics)

---

- **Genetic algorithm based material parameter analysis**
  - Establish a material basis set needed for atomistic simulations
- **Mechanical strain calculation**
  - Enable proper modeling of optical bandgaps
    - > proper tuning of optical transitions
- **Alloyed Dot simulation**
  - Enable simulation of realistic quantum dot compositions
  - Enable analysis of inhomogeneous linewidth broadening due to alloy disorder
- **Atomistic grading simulation**
  - Enable simulation of realistic quantum dot interfaces
  - Enable simulation of interface interdiffusion and the resulting modification of the confined quantum states.

*We are just starting to explore  
the capabilities of this simulator!*





## Technical Accomplishments (Software)

- **Parallelization**
  - Evaluate performance of 2 different parallel computing paradigms:
    - shared memory (all CPUs can access the same memory)
    - distributed memory (message passing between CPUs)
  - ⇒ performed a **2 million atom simulation** in the distributed model
  
- **Analysis of general molecular inputs -> Nanotubes**
  - Enable electronic simulation of “arbitrary” crystal structures generated from other structural simulators.
  - > Expansion to Moletronics

*3 person years of software work at JPL and 22 person years NEMO leverage enabled the simulation capabilities.*





# NASA Mission Requirements



- High radiation tolerance
- Extreme temperature operation
- Low weight, low power, high performance, high capacity

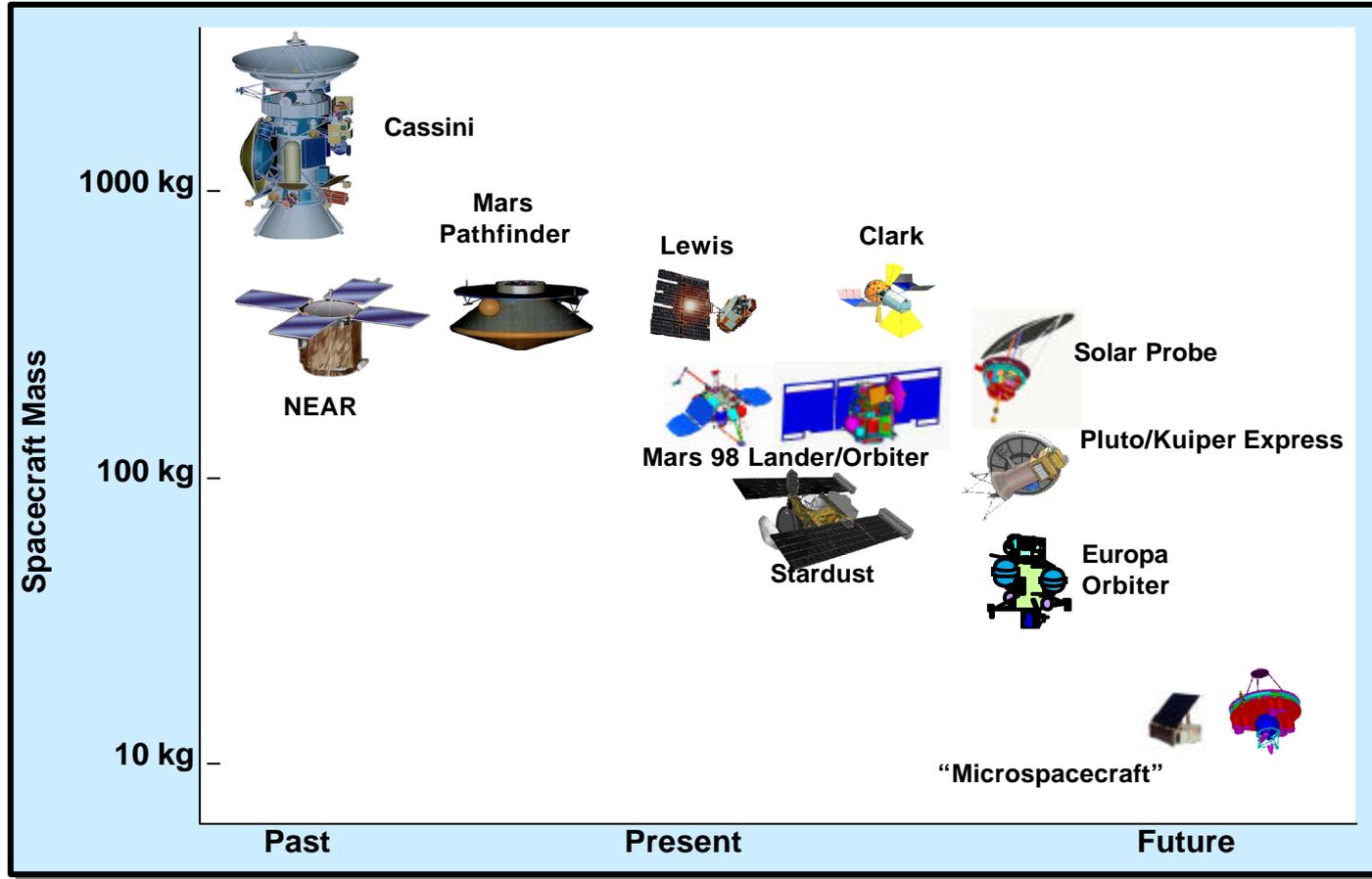


*NASA missions require systems that currently do not exist*





# Progressive Spacecraft Miniaturization



*Low weight, low power and high efficiency  
Have a special meaning to NASA*



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# Need for Nanoelectronic Simulation

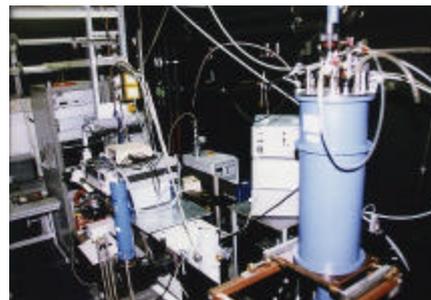
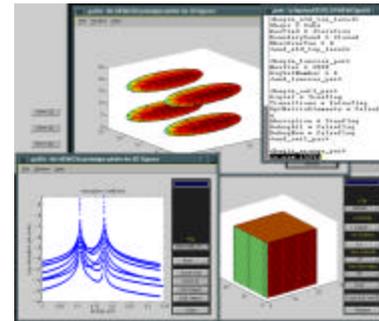
## Problems:

- Design space is huge
  - Choice of materials, shapes, orientations, dopings, heat anneals
- Characterizations are incomplete and invasive / destructive

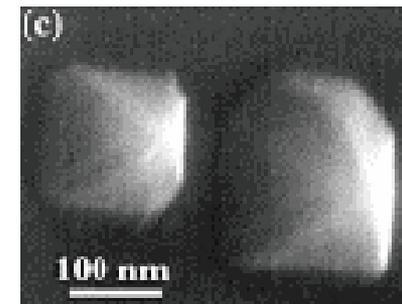
## Simulation Impact:

- Aide Design
  - Fast, cost effective.
  - > **Device performance**  
already successful for 1-D quantum devices
- Aide Characterization
  - Non-invasive
  - More accurate
  - > **Structure and doping analysis**  
already successful for 1-D quantum devices

## Simulation



Characterization



Fabrication

*Modeling, Characterization and Fabrication are inseparable for nanoscale devices*





# Nanotechnology Project Portfolio



- **Modeling**
  - Enable the exploration of the nanotechnology design space.
- **Characterization**
  - Optical, structural, transport and radiation testing.
- **Devices**
  - **Lasers / Output:**  
Enable radiation hard, narrow linewidth tunable lasers.
  - **Sensors / Input:**  
Enable acoustic and electronic sensors based on nanotubes.
  - **Memory:**  
Enable high density, low power, non-volatile, radiation hard storage.
- **Architectures:**
  - Enable massively parallel and fault tolerant computing architectures.



*Future deep space applications will directly benefit from directed nanotechnology research*





## Related Work

Investigator	Location	Hamiltonian	Atomistic	Many-Body	Extendable to Molecules?
Pryor	Lund	$k \cdot p$	NO	YES	NO
Bimberg	Berlin	$k \cdot p$	NO	NO	NO
Freund	Brown	$k \cdot p$	NO	NO	NO
Leburton	Illinois	1 Band	NO	NO	NO
Zunger	NREL	Pseudopotential	YES	NO	NO
Bowen/Klimeck	JPL	Tight-binding	YES	NO*	YES

\* - Planned for 01

Why JPL? JPL has expertise and infrastructure to tackle such large problems.

*We are in an excellent position to simulate molecular electronics from the bottom -up*





## Objective

- **Long term objective:**
  - Develop and demonstrate a physics-based, atomistic simulation tool for semiconductor quantum dots and molecular based electronic devices
- **Near term objective:**
  - Develop this year the technology necessary to simulate optical transitions in a single quantum dot
- **Tasks in FY 00:**
  - Alloyed dot simulation (04/00)
  - Shared memory parallelization (05/00)
  - 3-D visualization (05/00)
  - Atomistic grading simulation (07/00)
  - Atomistic impurity simulation (09/00)

*We build a bottom-up, atomistic  
nanoelectronic design tool*





# Software Structure Prototype/Vision

## Objective:

- Design, develop, test and deliver an interactive quantum dev. design tool
- Customers: Experimentalists not Simulation Specialists !

## Problem:

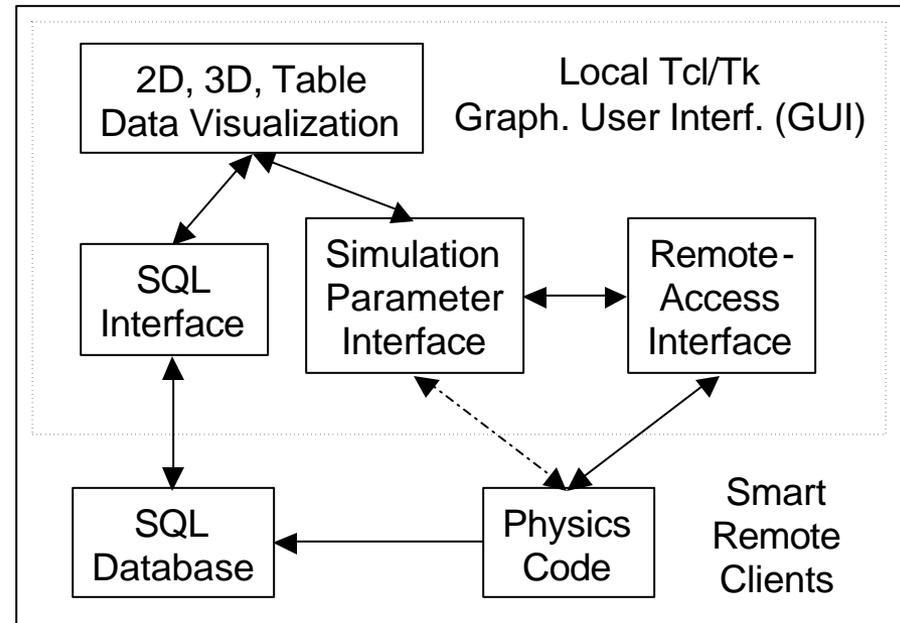
- Simulations are CPU intensive -> need supercomputers
- Datasets are typically 4-dim -> need custom visualization
- Local workstations are PC, MAC, SUN or SGI -> need portable Graph. User Interf.
- Input requirements change fast -> need dynamic GUI design

## Approach:

- Heterogeneous client-server Tcl/Tk-based GUI

## Impact:

- Using this approach on 2 completely independent simulators with little additional development time.



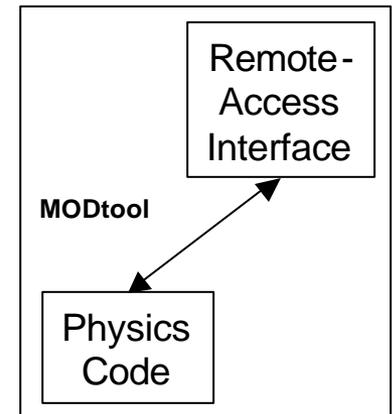
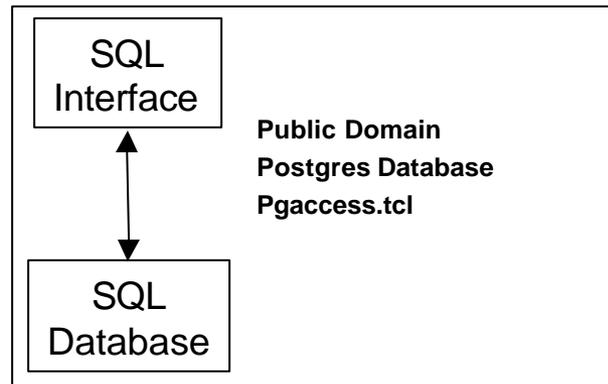
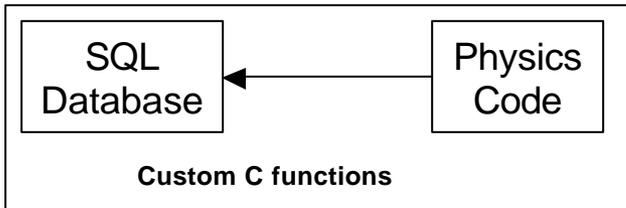
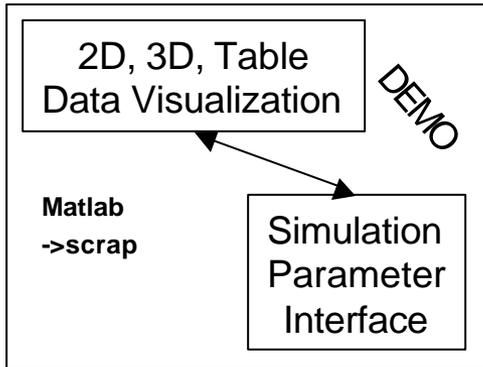
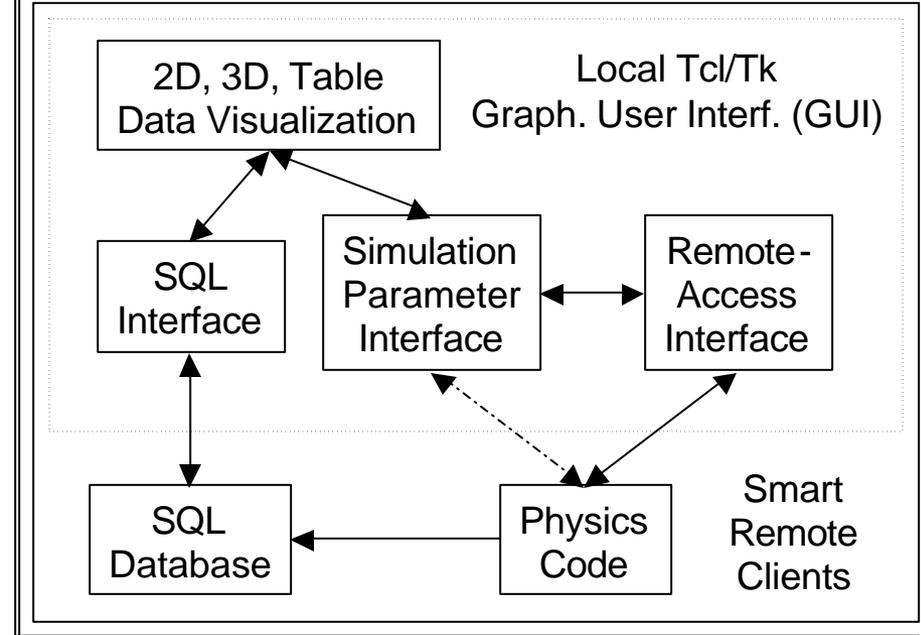
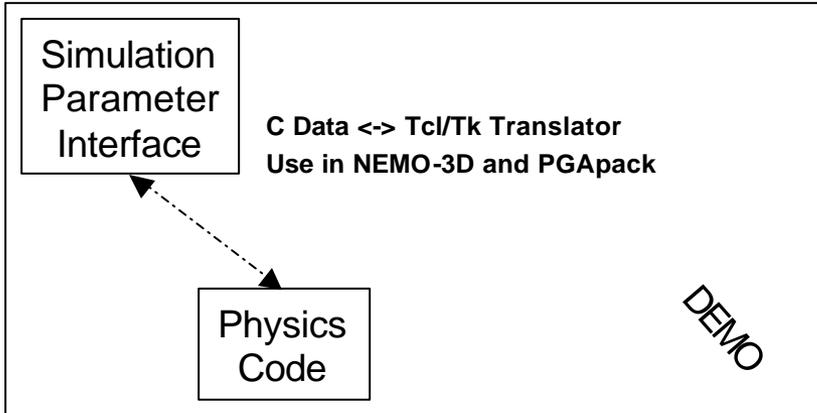
## Smarts are OUTSIDE the GUI:

- Physics code contains I/O structures
- Database completely general
- > GUI retrieves I/O structures and data from smart clients.
- > Flexibility for user and developer

*Flexible software design enables use in various different simulators*



# Software Structure Status



*Have built most of the essential components, need to go through integration process.*





### Objectives:

#### COMPUTERS

- Quantum Dots can enable new types of computing architectures (for example QCA).

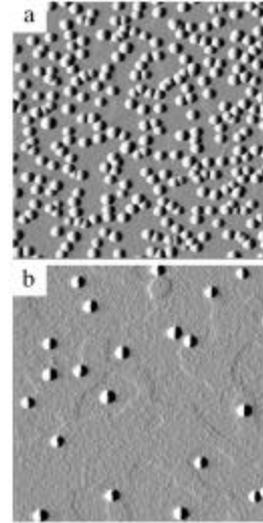
#### MEMORIES

- QDs can be used in ultra-high density optical memories.

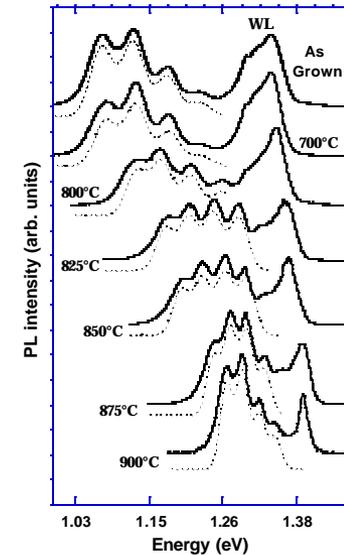
#### RADIATION TOLERANCE

- QDs enable radiation-hard opto-electronic devices.

### InGaAs Quantum Dots



Squares are 1 μm by 1 μm



Tuning inter-sublevel energies in Quantum Dots

### Approach:

- Achieve positional order of Quantum Dots (QDs) by combining patterning and various types of growth experiments.**
- Implement experimental capabilities for in-house QD characterization.**
- Collaborate with Universities on fabrication, growth experiments, and characterization.**
- Perform tests and experiments on existing QD structures - understand QD properties and how they impact their various device applications.**



# Quantum Dot Fabrication for Lasers

Task Lead: Yueming Qiu

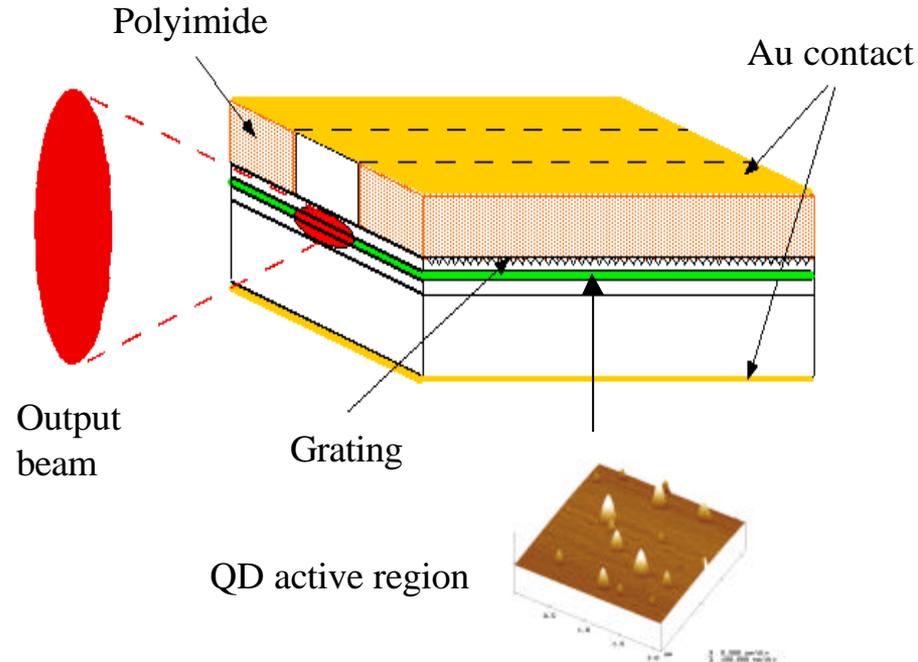


## Objective:

- Design and fabricate high efficient, low power consumption, radiation hard QD based optoelectronic devices, such as:
  - lasers
    - ultralow threshold current density
    - temperature insensitive
    - narrow linewidth

## NASA applications:

- Large format, low noise IR detector arrays are enabling technology for SSE
- Broad area of applicability:
  - Spectroscopy
  - Microinstruments
  - Communications
  - LIDAR and Interferometry



## Collaborators:

- University of New Mexico





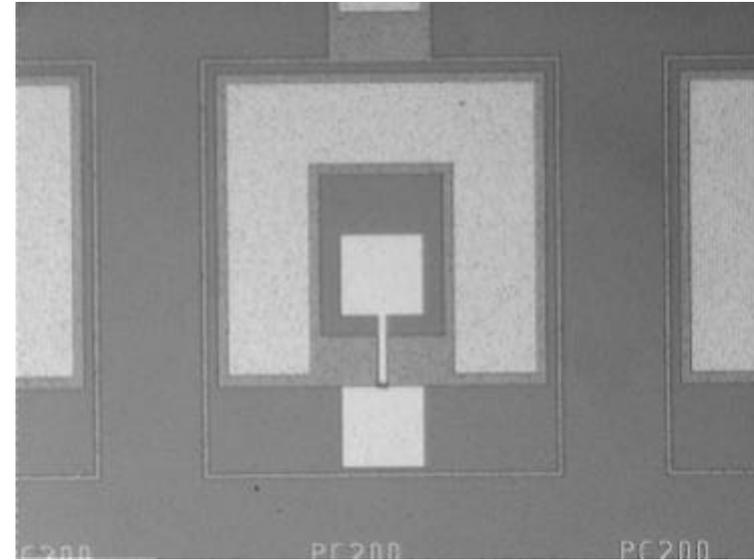
# Single Electron Nonvolatile Memory

Task Lead: Doug Bell



## Task Purpose/Objectives:

- Develop a *room-temperature, radiation-tolerant* memory technology based on single-electron storage.
- Decrease read/write time by orders of magnitude using a novel peaked-tunnel-barrier concept.
- Increase capability for computing storage by increasing storage density and decreasing storage power.



## Major Products:

- Silicon nanocrystal floating-gate memory
- Shape-engineered tunnel barrier for breakthrough read/write speed.

## NASA Relevance:

- **Space Science:** (autonomous spacecraft systems and robots)
- **Earth Science:** (autonomous navigation / guidance; sensing and sensor webs)
- **Human Exploration:** (autonomous robotic monitoring systems)

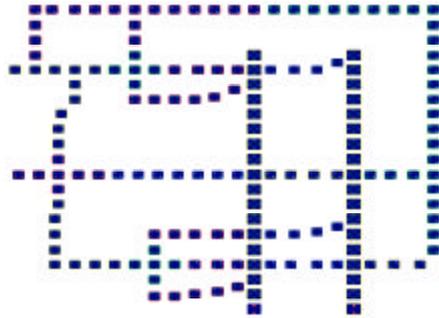




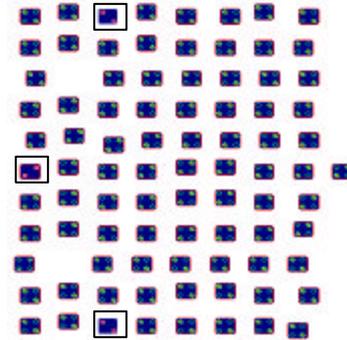
# Quantum Dots Based Computing:

## Quantum Dots Cellular Automata (QCA) Architectures and Applications

Task Lead: Amir Fijani



Novel QCA Circuits: A Bit-Serial Adder



Novel QCA Gates: Fault Tolerant Majority Gate

### Objective:

- Develop new logic gates and circuits with emphasis on fault tolerance capabilities.
- Develop massively parallel computing architectures by exploiting inherent features of QCA.

### Accomplishments:

- Alternative design of highly fault tolerant logic gates based on arrays of QCA.
- Massively parallel computing architectures for a set of signal/image processing applications.

### NASA Relevance:

- Enable smaller and smarter spacecraft by providing drastic improvement over VLSI technology in terms of
  - Integration density
  - Mass, volume, and power consumption
  - Radiation tolerance
  - Enabling novel applications

### External Collaborators:

- University of Notre Dame
- Oak Ridge National Laboratory

**QCA: A totally new computing paradigm**

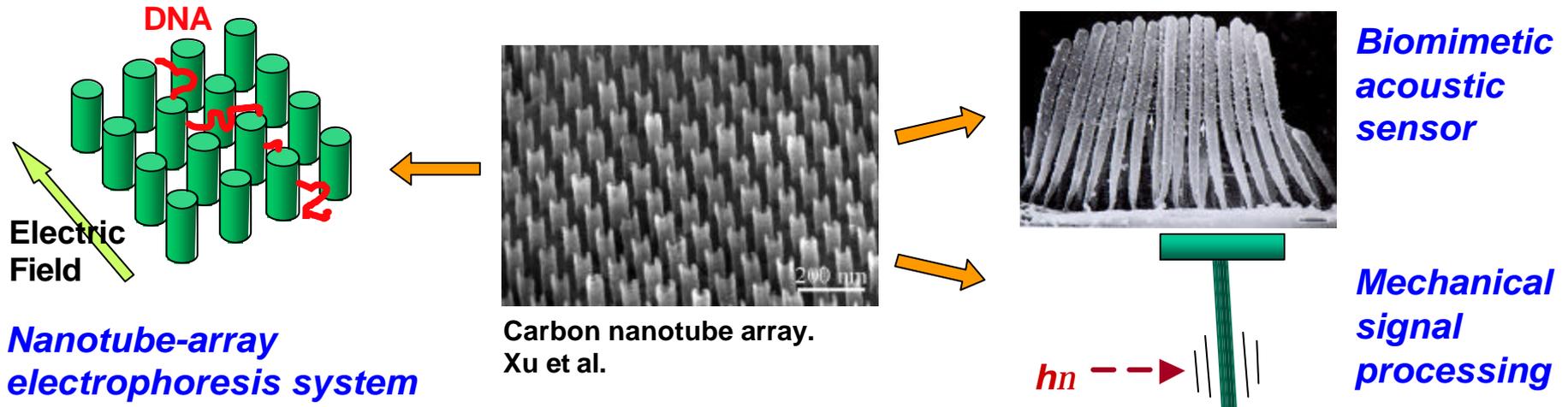
**Challenges: Architecture and Application Design, Fault Tolerance**





# Bio-Inspired Nanotube Array Applications

Task Lead: Brian Hunt



## Motivation / Impact:

- Nanotubes combine useful properties and nanoscale dimensions
- NT-based electro-mechanical devices provide enabling technology for NASA missions: e.g., biomolecular probes, nanoexplorers

## Objective:

### *Demonstrate prototype nanotube-based devices*

- ♦ NT electrophoresis system
- ♦ Biomimetic acoustic sensor
- ♦ NT actuators
- ♦ NT high-Q resonators
- ♦ NT electronic components

## NASA Applications:

- Search for life via acoustic and molecular signatures
- Nanoscale fabrication and characterization
- Revolutionary computing components
- Intense electron sources



gekco





## Motivation / Customers

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- **NASA Relevance:**
  - Enable devices needed for NASA missions beyond existing industry roadmap:
    - 2-5 $\mu$ m lasers and detectors
    - High density, low power computation (logic and memory)
    - Life signature biosensors
- **Impact:**
  - Low cost development of revolutionary technology.
  - Narrow empirical/experimental search space
- **Customers / Missions:**
  - CISM
  - MDL
  - HPCC





## Potential Benefits / Payoffs

---

### **NASA Relevance:**

- **2-5mm Lasers and detectors**
- **High density, low power computation (logic and memory)**
- **Life signature biosensors**

### **Impact:**

- **Narrow empirical/experimental search space**
- **Low cost development of revolutionary technology.**





# Delivery of a Simulation Tool



The screenshot displays the NEMO3D simulation tool interface, which is divided into several windows:

- gui3d: the NEMO3D prototype plotter for 3D figures**: Shows a 3D visualization of four elongated, rod-like structures. The axes range from 0 to 25. Buttons for "View 2D", "View 3D", and "Run Calc" are visible on the left.
- gui2d: the NEMO3d prototype plotter for 2D Figures**: Displays a 2D plot titled "Absorption Coefficient". The y-axis is "Log Absorption (arb units)" ranging from -14 to -5. The x-axis is "Energy (eV)" ranging from 0 to 0.35. The plot shows multiple curves with peaks. A control panel on the right includes buttons for "File", "AbsCoeff\_2d", "Print", "Zoom Out", "Zoom In", "Kill Object", "Edit Object", and "Draw".
- Code Editor (polo : lu1/gekco/DEVELOP/NEMO/gui3d)**: Contains the following code:

```
<begin_n3d_top_level>
Shape = Cube
ResFind = Iterative
BoundaryCond = Closed
HbarOverTau = 0
<end_n3d_top_level>

<begin_lanczos_par>
MaxIter = 2000
EigValNumber = 8
<end_lanczos_par>

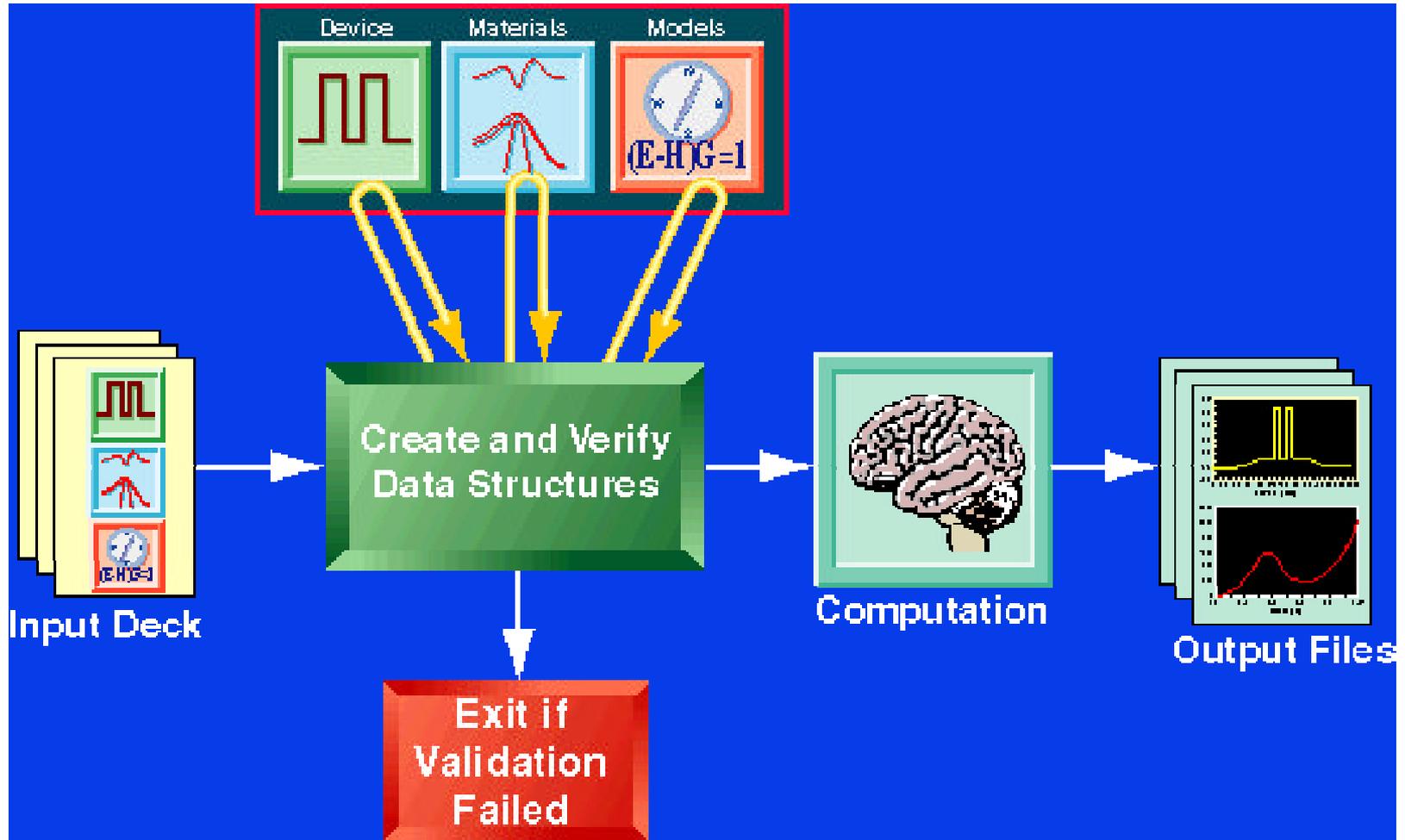
<begin_out1_par>
Eigval = Trueflag
Transitions = Falseflag
OptMatrixElements = Falseflag
Absorption = Trueflag
DebugAll = Falseflag
DebugNow = Falseflag
<end_out1_par>

<begin_orange_par>
in.nem (50%)
```
- 3D Grid View**: Shows a 3D grid of a cube with a color gradient from green to red. A control panel on the right includes buttons for "File", "domain", "Colormap", "1 copper", "Iso Surface", "0.1", "View Azimuth: -37", "View Elevation: 30", "Print", "Free Rot On/Off", and "Redraw".



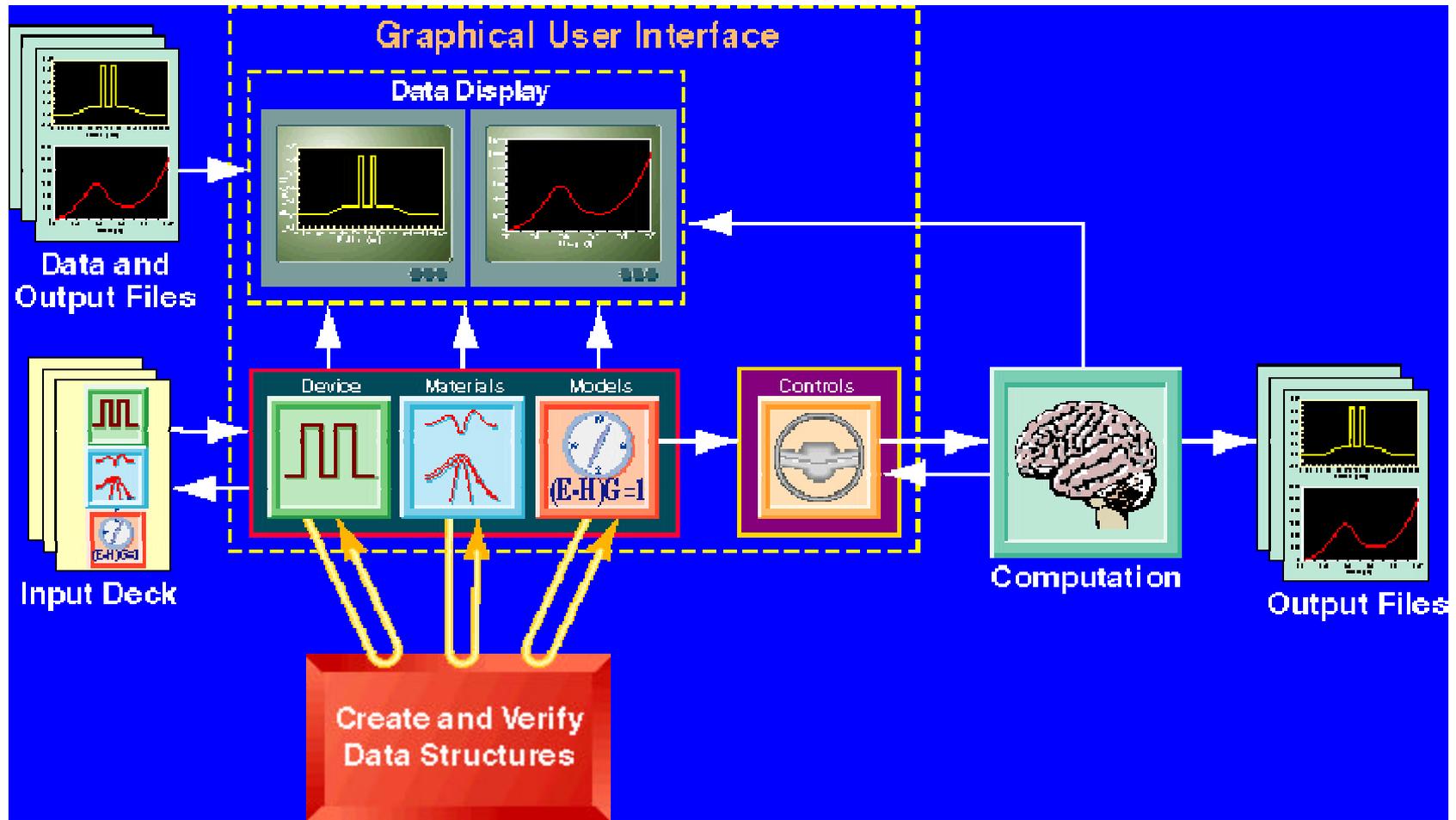


# Batch Dataflow is Linear





# GUI Data Flow is Continuous



**GUI interacts with different software blocks continuously**





# Hierarchical Ordering of User Input



Semi-class. self-cons. pot. & single band current
Specify desired outputs
Quantum region: "Where are wave-functions?"
Non-equilibrium region: "Where are the reservoirs?"
Adaptive energy grid
-----
-----
-----

Quantum self-cons. potential & single band current
exchange & correlation?
how to go from bias to bias?
Specify desired outputs
Quantum region: "Where are wave-functions?"
Non-equilibrium region: "Where are the reservoirs?"
Quantum Charge region: "Where is the charge quantum mechanically calculated?"
Resonances-based energy grid
-----
-----
-----

Ask user for input that is really needed.  
 -> User input determines the sequence of simulation parameter windows.

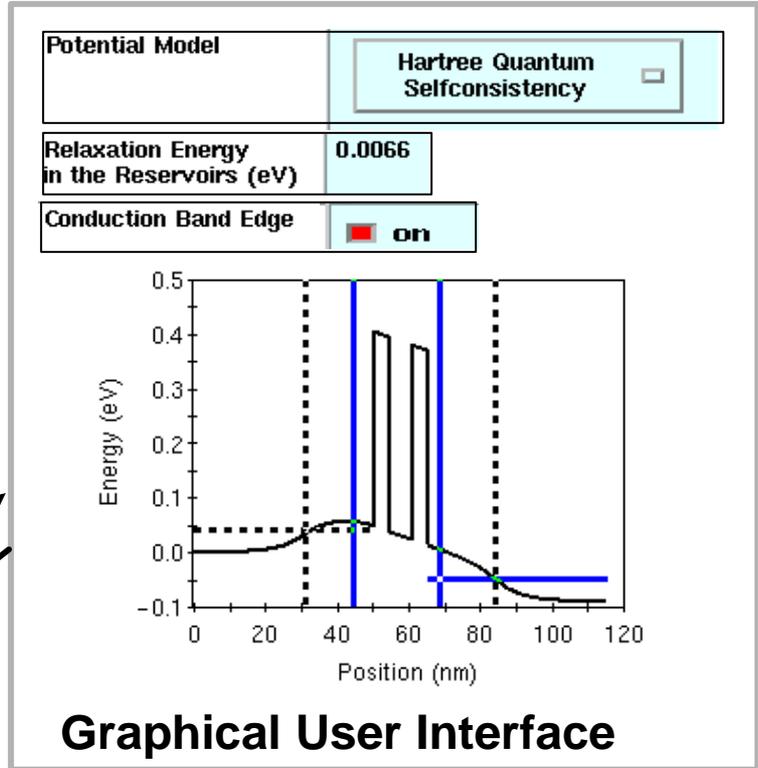




# Generic Data Structure I/O

## Dynamic GUI Design.

- data structure
- member descriptor
- > I/O for GUI or files



Graphical User Interface

```

File/Batch User Interface
potential=Hartree
hbarovertau=0.0066
Ec=FALSE
< start=45, end=69 >

```

**Data Structure**  
 PotType potential  
 real hbarovertau  
 Boolean Ec  
 RangeStruct NonEq

**Translator**

**Theorist**

**Software Engineer**

